BarÄ±Å KÄ±nacÄ±

List of Publications by Year
in descending order

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22	374	840776	794594
papers	citations	11	19
		h-index	g-index

22	22	22	302
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Dielectric Properties of Au/SrTiO3/p-Si Structure Obtained by RF Magnetron Sputtering in a Wide Frequency Range. Silicon, 2022, 14, 2717-2722.	3.3	6
2	Influence of V2O5 and B2O3 addition on the sintering behaviour and physical properties of ZnO ceramics. Processing and Application of Ceramics, 2022, 16, 48-54.	0.8	1
3	Evaluation of dielectric properties of Au/TZO/nâ€“Si structure depending on frequency and voltage. Journal of Materials Science: Materials in Electronics, 2022, 33, 10516-10523.	2.2	3
4	Functional optical design of thickness-optimized transparent conductive dielectric-metal-dielectric plasmonic structure. Scientific Reports, 2022, 12, .	3.3	9
5	The temperature dependent negative dielectric constant phenomena of Au/nâ€“GaAs structure with CZO interfacial layer. Journal of Materials Science: Materials in Electronics, 2021, 32, 5928-5935.	2.2	4
6	Modeling and Experimental Analysis of Photovoltaic Parameters of GaInP/GaAs Dual Junction pâ€“iâ€“n Solar Cell. Brazilian Journal of Physics, 2021, 51, 553-558.	1.4	3
7	Determination of surface morphology and electrical properties of MoO3 layer deposited on GaAs substrate with RF magnetron sputtering. Journal of Materials Science: Materials in Electronics, 2021, 32, 12330-12339.	2.2	9
8	Design and fabrication of a semi-transparent solar cell considering the effect of the layer thickness of MoO3/Ag/MoO3 transparent top contact on optical and electrical properties. Scientific Reports, 2021, 11, 13079.	3.3	25
9	Structural, morphological, optical and electrical properties of the Ti doped-ZnO (TZO) thin film prepared by RF sputter technique. Physica B: Condensed Matter, 2021, 616, 413126.	2.7	13
10	Investigation of the effect of annealing on the structural, morphological and optical properties of RF sputtered WO3 nanostructure. Physica B: Condensed Matter, 2021, 622, 413350.	2.7	11
11	Investigation of V-groove fabricated GaInNAs nipi solar cell structure. Optical and Quantum Electronics, 2021, 53, 1.	3.3	0
12	The effect of thickness on surface structure of rf sputtered TiO2 thin films by XPS, SEM/EDS, AFM and SAM. Vacuum, 2020, 182, 109766.	3.5	68
13	A comprehensive study on Cu-doped ZnO (CZO) interlayered MOS structure. Journal of Materials Science: Materials in Electronics, 2020, 31, 13646-13656.	2.2	18
14	Negative capacitance phenomena in Au/SrTiO3/p-Si heterojunction structure. Journal of Materials Science: Materials in Electronics, 2020, 31, 8718-8726.	2.2	14
15	Characterization of a GaAs/GaAsBi pin solar cell. Semiconductor Science and Technology, 2019, 34, 085001.	2.0	14
16	V-groove etched 1-eV-GaInNAs nipi solar cell. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	2.3	6
17	Performance evaluation of a GaInP/GaAs solar cell structure with the integration of AlGaAs tunnel junction. Solar Energy Materials and Solar Cells, 2015, 137, 1-5.	6.2	36
18	AZO thin film-based UV sensors: effects of RF power on the films. Applied Physics A: Materials Science and Processing, 2015, 119, 965-970.	2.3	24

#	Article	IF	Citations
19	Analysis of the Temperature Dependence of the Capacitanceâ€“Voltage and Conductanceâ€“Voltage Characteristics of Au/TiO2(rutile)/n-Si Structures. Journal of Electronic Materials, 2013, 42, 1108-1113.	2.2	21
20	The temperature dependent analysis of Au/TiO2 (rutile)/n-Si (MIS) SBDs using currentâ€“voltageâ€“temperature (Iâ€“Vâ€“T) characteristics. Materials Science in Semiconductor Processing, 2012, 15, 531-535.	4.0	36
21	Analysis of the forward and reverse bias I-V characteristics on Au/PVA:Zn/n-Si Schottky barrier diodes in the wide temperature range. Journal of Applied Physics, 2011, 109, .	2.5	48
22	Effect of different P/As ratio on the optical and structural properties of GaAs_{1â^'x}P_x/GaAs. Surface and Interface Analysis, 2010, 42, 1252-1256.	1.8	5